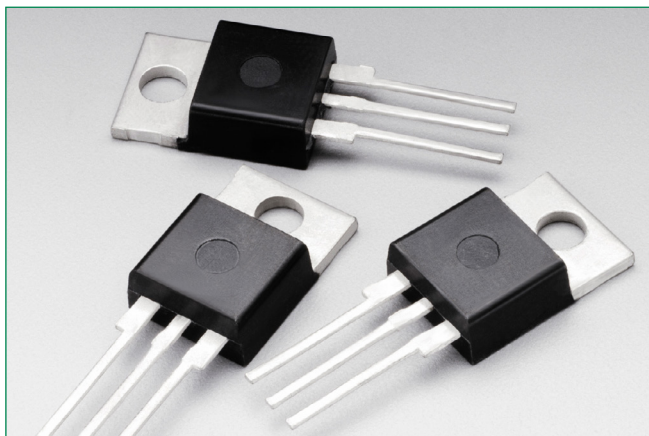


BTB08-600CW3G, BTB08-800CW3G

Surface Mount – 600 - 800V

**Description**

The BTB08 is designed for high performance full-wave AC control applications where high noise immunity and high commutating di/dt are required.

Features

- Blocking Voltage to 800 V
- On-State Current Rating of 8 A RMS at 80°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dV/dt – 1500 V/μs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating di/dt – 3.0 A/ms minimum at 125°C
- These Devices are Pb-Free

Additional Information

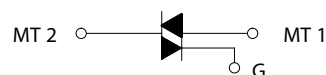
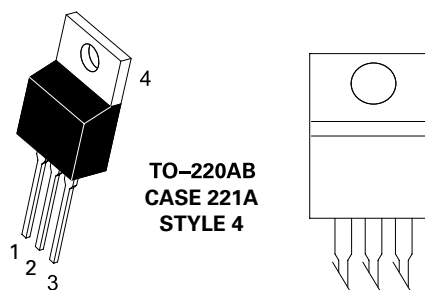
Resources



Accessories



Samples

Functional Diagram**Pin Out**

BTB08-600CW3G, BTB08-800CW3G

Surface Mount – 600 - 800V

Maximum Ratings † (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	V _{DRM} [*] V _{RRM}	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T _c = 80°C)	I _{T (RMS)}	8.0	A
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _c = 25°C)	I _{TSM}	90	A
Circuit Fusing Considerations (t = 10 ms)	I ² t	36	A ² sec
Non-Repetitive Surge Peak Off-State Voltage (T _J = 25°C, t = 10ms)	V _{DSM} /V _{RSM}	V _{DSM} /V _{RSM} + 100	V
Peak Gate Current (T _J = 125°C, t = 20ms)	I _{GM}	4.0	A
Peak Gate Power (Pulse Width ≤ 1.0 μs, T _c = 80°C)	P _{GM}	20	W
Average Gate Power (T _J = 125°C)	P _{G(AV)}	1.0	W
Operating Junction Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +125	°C

† Indicates JEDEC Registered Data

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Maximum Ratings † (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (AC) Junction-to-Ambient	R _{θJC} R _{θJA}	2.5 60	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T _L	260	°C

† Indicates JEDEC Registered Data

Electrical Characteristics - OFF (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Repetitive Blocking Current (V _D = V _{DRM} = V _{RRM} ; Gate Open)	I _{DRM} [*] I _{RRM}	-	-	0.005 1.0	mA

Electrical Characteristics - ON

Characteristic	Symbol	Min	Typ	Max	Unit
Peak On-State Voltage (Note 2) (I _{TM} = ±11 A Peak)	V _{TM}	-	-	1.55	V
Gate Trigger Current (Continuous dc) (V _D = 12 V, R _L = 30 Ω)	MT2(+), G(+)	2.5	-	35	mA
	MT2(+), G(-)	2.5	-	35	
	MT2(-), G(-)	2.5	-	35	
Holding Current (V _D = 12 V, Gate Open, Initiating Current = ±100 mA)	I _H	-	-	45	mA
Latching Current (V _D = 24 V, I _G = 42 mA)	MT2(+), G(+)	-	-	50	mA
	MT2(+), G(-)	-	-	80	
	MT2(-), G(-)	-	-	50	
Gate Trigger Voltage (V _D = 12 V, R _L = 30 Ω)	MT2(+), G(+)	0.5	-	1.7	V
	MT2(+), G(-)	0.5	-	1.1	
	MT2(-), G(-)	0.5	-	1.1	
Gate Non-Trigger Voltage (T _J = 125°C)	MT2(+), G(+)	0.2	-	-	V
	MT2(+), G(-)	0.2	-	-	
	MT2(-), G(-)	0.2	-	-	

2. Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

BTB08-600CW3G, BTB08-800CW3G

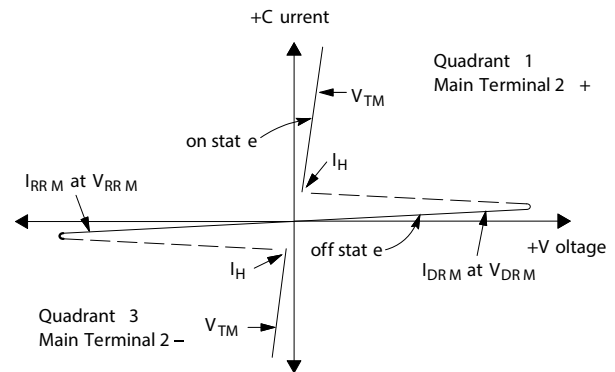
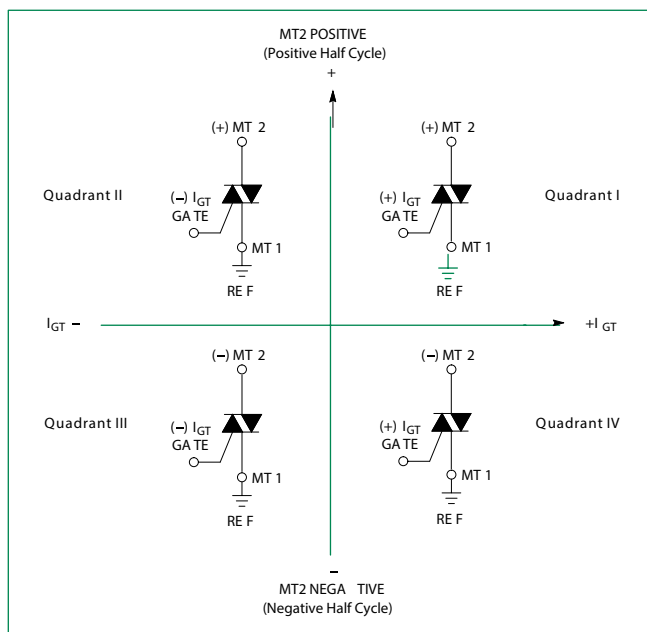
Surface Mount – 600 - 800V

Dynamic Characteristics

Characteristic	Symbol	Min	Typ	Max	Unit
Rate of Change of Commutating Current, See Figure 10. (Gate Open, $T_J = 125^\circ\text{C}$, No Snubber)	$(di/dt)_c$	3.0	–	–	A/ms
Critical Rate of Rise of On-State Current ($T_J = 125^\circ\text{C}$, $f = 120\text{ Hz}$, $I_G = 2 \times I_{GT}$, $tr \leq 100\text{ ns}$)	di/dt	–	–	50	A/ μs
Critical Rate of Rise of Off-State Voltage ($V_D = 0.66 \times V_{DRM}$, Exponential Waveform, Gate Open, $T_J = 125^\circ\text{C}$)	dV/dt	1500	–	–	V/ μs

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current

**Quadrant Definitions for a Triac**

All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used

BTB08-600CW3G, BTB08-800CW3G

Surface Mount – 600 - 800V

Figure 1. RMS Current Derating

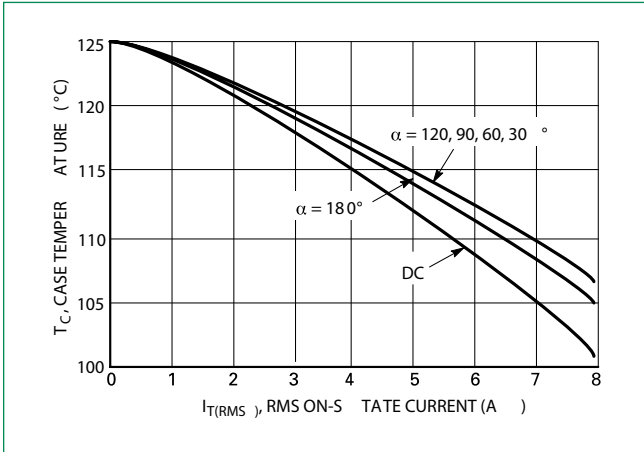


Figure 2. On-State Power Dissipation

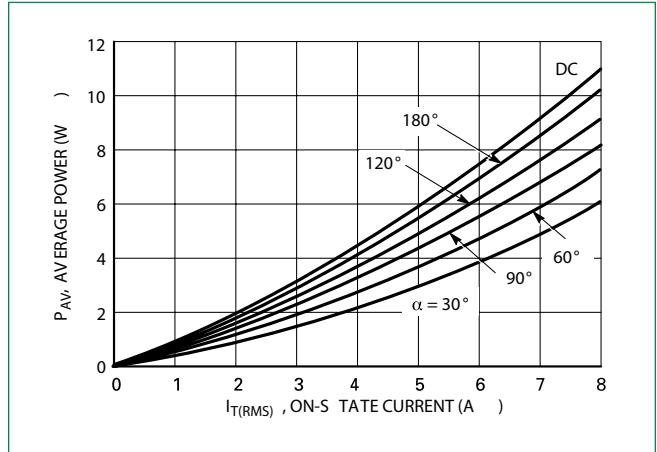


Figure 3. On-State Characteristics

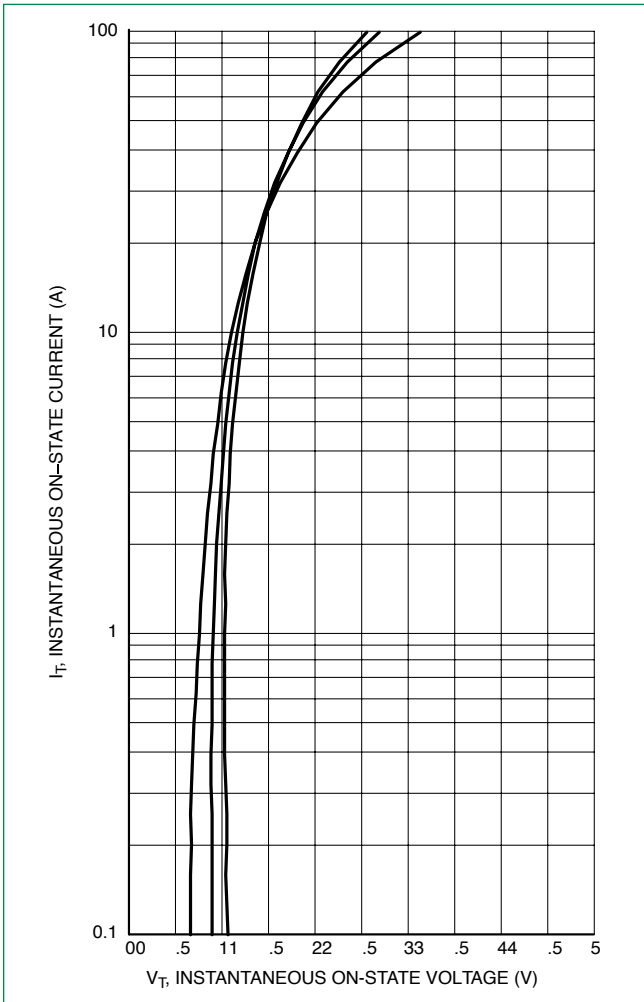


Figure 4. Thermal Response

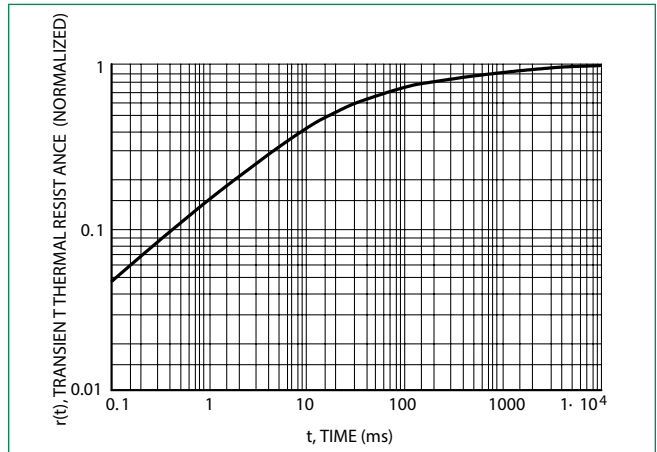
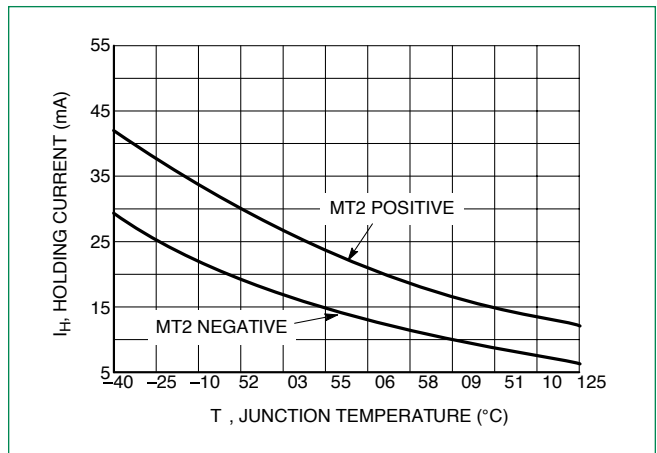


Figure 5. Hold Current Variation



BTB08-600CW3G, BTB08-800CW3G

Surface Mount – 600 - 800V

Figure 6. Gate Trigger Current Variation

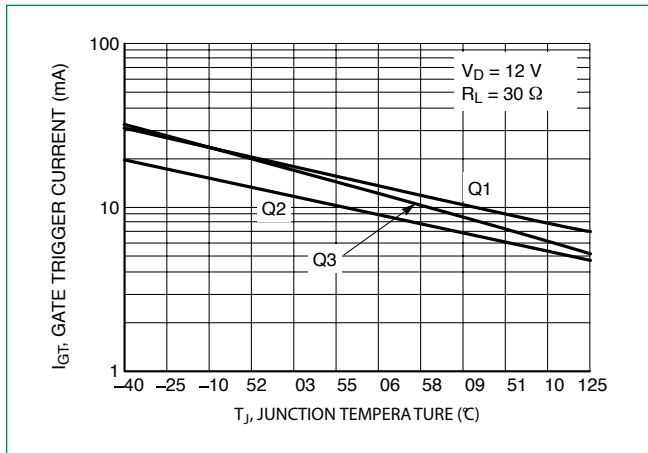


Figure 7. Gate Trigger Voltage Variation

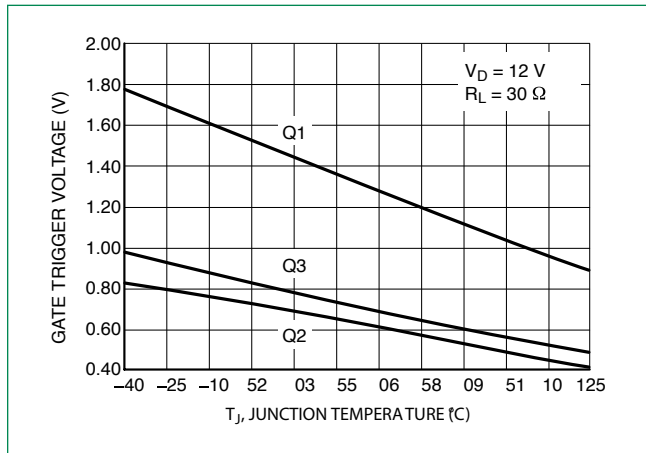


Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential Waveform)

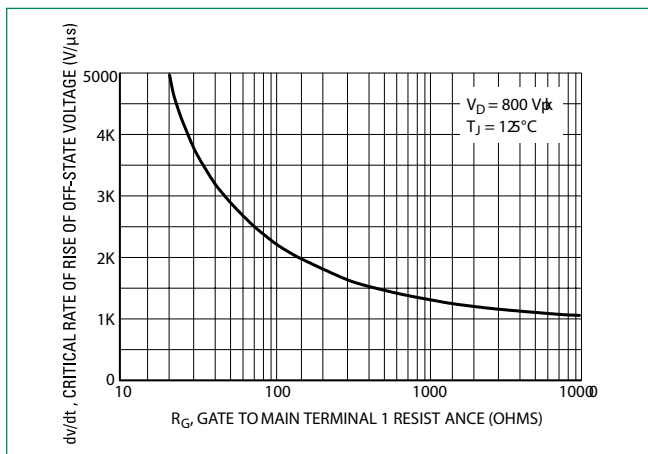


Figure 10. Latching Current Variation

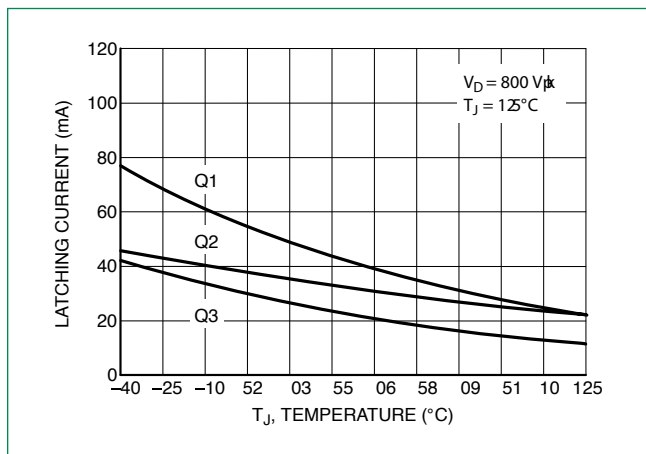
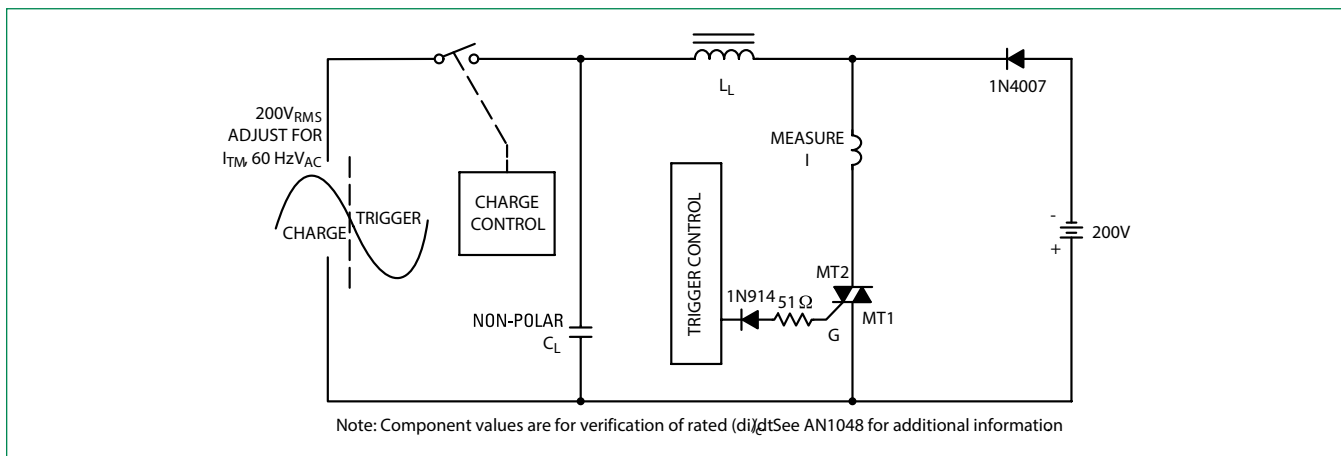


Figure 9. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)



Note: Component values are for verification of rated (di/dt). See AN1048 for additional information